Title (en)

METHOD FOR METALLIZING THE PREVIOUSLY PASSIVATED SURFACE OF A SEMICONDUCTOR MATERIAL AND RESULTING MATERIAL

Title (de)

VERFAHREN ZUR METALLISIERUNG DER ZUVOR PASSIVIERTEN OBERFLÄCHE EINES HALBLEITERMATERIALS UND AUF DIESE WEISE HERGESTELLTES MATERIAL

Title (fr)

PROCEDE DE METALLISATION DE LA SURFACE PREALABLEMENT PASSIVEE D'UN MATERIAU SEMICONDUCTEUR ET MATERIAU OBTENU PAR CE PROCEDE

Publication

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Application

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Priority

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Abstract (en)

[origin: WO2006005869A1] The invention concerns a method for metallizing the previously passivated surface of a semiconductor material and resulting material. The invention, which is applicable in microelectronics, is characterized in that it consists in: preparing the surface of the material (2) so that it contains bonds capable of absorbing hydrogen atoms or a metal element, passivating one or more layers, preferably immediately underlying the surface, by exposing same to a passivating compound, and metallizing the surface (4) by exposing same to hydrogen atoms or the metal element.

IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

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